

**Vishay Siliconix** 

# Automotive N-Channel 75 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V <sub>DS</sub> (V)	75
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.026
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.032
I <sub>D</sub> (A)	30
Configuration	Single



## **FEATURES**

- TrenchFET<sup>®</sup> power MOSFET
- AEC-Q101 qualified <sup>d</sup>
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



RoHS COMPLIANT HALOGEN FREE

Top View	G Bottom View	S N-Channel MOSFET
ORDERING INFORMATI		
Package		PowerPAK SO-8L
Lead (Pb)-free and Halogen-free		SQJ486EP-T1-GE3

ABSOLUTE MAXIMUM RATING	<b>S</b> (T <sub>C</sub> = 25 °C, unless	otherwise noted	)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V <sub>DS</sub>	75	N/		
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Constitutions Design Comment &	T <sub>C</sub> = 25 °C	1	30		
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 125 °C	Ι <sub>D</sub>	17		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	50	А	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	120		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	13		
Single Pulse Avalanche Energy		E <sub>AS</sub>	9	mJ	
Marian m Darran Diaging tions b	T <sub>C</sub> = 25 °C	PD	56	W	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	۳D	19	vv	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering Recommendations (Peak Tempera	ture) <sup>e, f</sup>		260		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	70	°C/W
Junction-to-Case (Drain)		R <sub>thJC</sub>	2.7	0/10

### Notes

a. Package limited.

b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

c. When mounted on 1" square PCB (FR-4 material).

d. Parametric verification ongoing.

See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed e. copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

f. Rework conditions: Manual soldering with a soldering iron is not recommended for leadless components.

S14-1445-Rev. B, 14-Jul-14

1 For technical questions, contact: automostechsupport@vishay.com Document Number: 62902

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SQJ486EP

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = 250 μA	75	-	-	v
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.1	1.6	2.1	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, $V_{GS} = \pm 20 V$	-	-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 75 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	$V_{DS} = 75 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA
		$V_{GS} = 0 V$	$V_{DS} = 75 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	150	-
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	30	-	-	А
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5.9 A	-	0.022	0.026	
	Р	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5.9 A, T <sub>J</sub> = 125 °C	-	-	0.043	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 5.9 A, T <sub>J</sub> = 175 °C	-	-	0.056	Ω
		$V_{GS} = 4.5 V$	I <sub>D</sub> = 5.3 A	-	0.026	0.032	
Forward Transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> :	= 15 V, I <sub>D</sub> = 5.9 A	-	75	-	S
Dynamic <sup>b</sup>				•			
Input Capacitance	C <sub>iss</sub>			-	1109	1386	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 37 V, f = 1 MHz	-	146	183	pF
Reverse Transfer Capacitance	C <sub>rss</sub>				63	79	
Total Gate Charge <sup>c</sup>	Qg			-	22	34	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 37 \text{ V}, \text{ I}_{D} = 8 \text{ A}$	-	2.7	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	5	-	
Gate Resistance	R <sub>g</sub>		f = 1 MHz	0.45	0.9	1.5	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	9	13	
Rise Time <sup>c</sup>	t <sub>r</sub>	: חחV	= 37 V, $R_{L}$ = 30 $\Omega$	-	11	17	1
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>		$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	-	21	31	ns
Fall Time <sup>c</sup>	t <sub>f</sub>	1		-	14	21	1
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>	• 					
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	120	Α
	V <sub>SD</sub>	I <sub>F</sub> = 3.9 A, V <sub>GS</sub> = 0			0.76	1.2	v

### Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

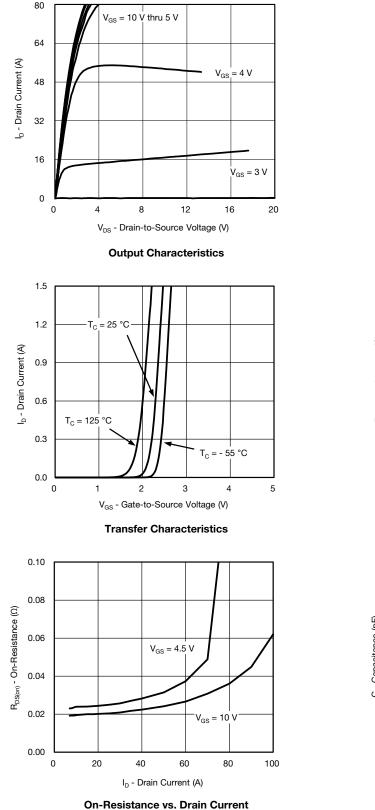
c. Independent of operating temperature.

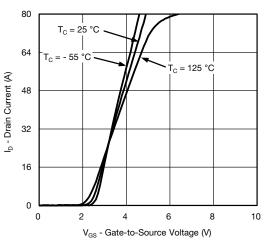
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

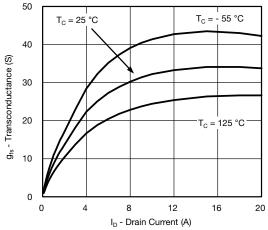


## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

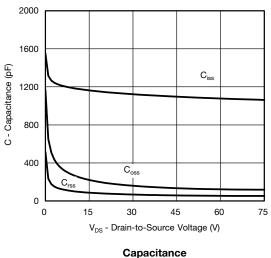




**Transfer Characteristics** 



Transconductance



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3

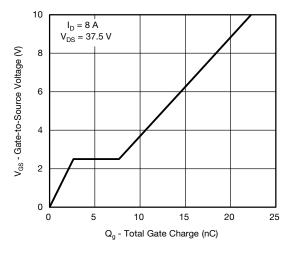
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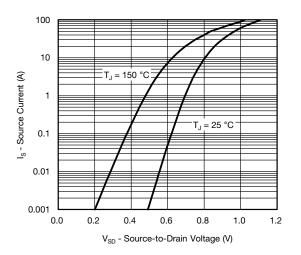


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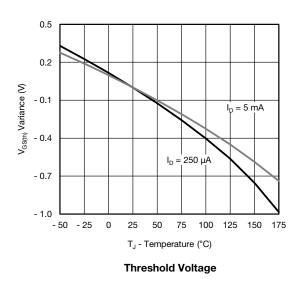
## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

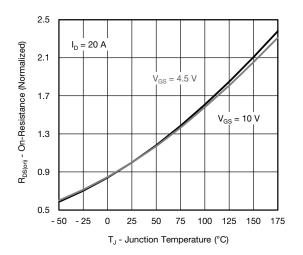


Gate Charge

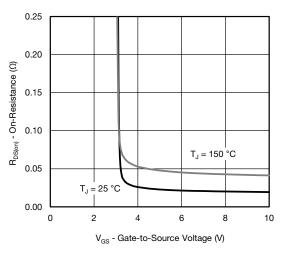


Source Drain Diode Forward Voltage

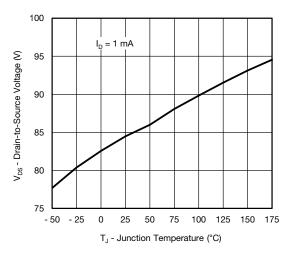




**On-Resistance vs. Junction Temperature** 



**On-Resistance vs. Gate-to-Source Voltage** 



Drain Source Breakdown vs. Junction Temperature

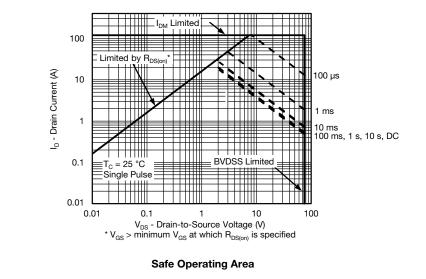
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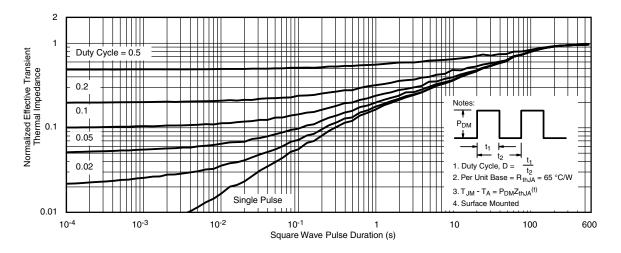
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## **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



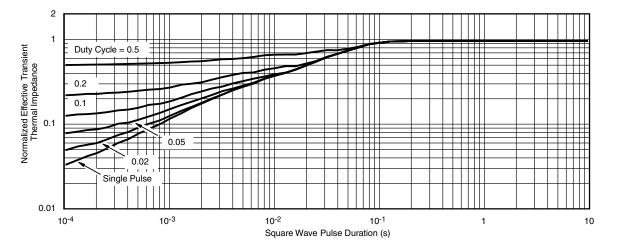


Normalized Thermal Transient Impedance, Junction-to-Ambient



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## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?62902">www.vishay.com/ppg?62902</a>.



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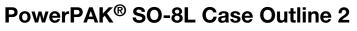
### **REVISION HISTORY**<sup>a</sup>

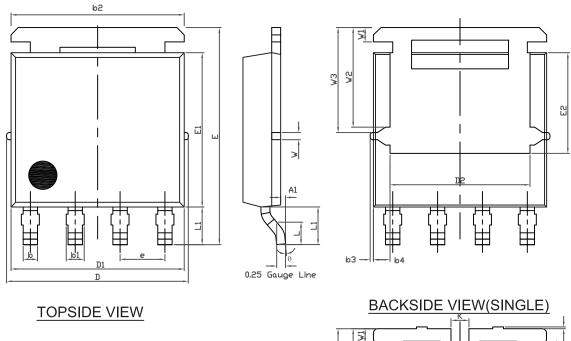
REVISION DATE DESCRIPTION OF CHANGE	
B 08-Jul-14 • Pin 2 in pin-out diagram corrected to S for source	

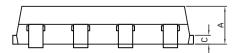
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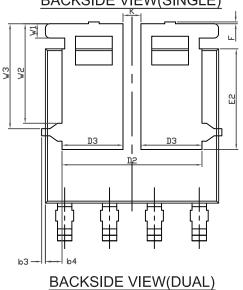
a. As of April 2014











# **Package Information**



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DIM	MILLIMETERS				INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094		0.004			
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К		0.51			0.020		
W		0.23			0.009		
W1	0.41			0.016			
W2		2.82			0.111		
W3		2.96			0.117		
q	0°	-	10°	0°	-	10°	

Note

• Millimeters will gover



## RECOMMENDED MINIMUM PAD FOR PowerPAK<sup>®</sup> SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12

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